

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

Claims 1-21 (canceled)

Claim 22 (currently amended): A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, consisting essentially of ~~comprising~~:

forming a solution by combining HF with a concentration of 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of 29%-30% in deionized water wherein said forming a solution further comprises using a volume ratio greater than 1:1:20 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water; and

applying said solution to said semiconductor body with said solution being at room temperature.

Claim 23 (currently canceled):

Claim 24 (currently amended): A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, consisting essentially of:

forming a solution by combining HF with a concentration of 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of 29%-30% in deionized water

~~The method of claim 22~~ wherein said forming a solution further comprises using a volume ratio of 2:1:21 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water; and

applying said solution to said semiconductor body with said solution being at room temperature.

Claim 25 (original): The method of claim 22 wherein said method further comprises applying said solution in the presence of photoresist.

Claim 26 (currently amended): A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, consisting essentially of comprising:

forming a solution by combining HF with a concentration of 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of 29%-30% in deionized water wherein said forming a solution further comprises using a volume ratio greater than 1:1:20 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water ; and

applying said solution to said semiconductor body with said solution being at a temperature of 40°C to 50°C.

Claim 27 (currently canceled)

Claim 28 (currently amended): A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, consisting essentially of:

forming a solution by combining HF with a concentration of 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of 29%-30% in deionized water

~~The method of claim 26~~ wherein said forming a solution further comprises using a volume ratio of 2:1:21 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water; and

applying said solution to said semiconductor body with said solution being at a temperature of 40°C to 50°C.

Claim 29 (original): The method of claim 26 wherein said method further comprises applying said solution in the presence of photoresist.

Claim 30 (added): The method of claim 28 wherein said method further comprises applying said solution in the presence of photoresist.

Claim 31 (added): The method of claim 24 wherein said method further comprises applying said solution in the presence of photoresist.